Improved understanding of the role of strained structure in degradation of surface superconductivity of superconducting RF quality niobium

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Motivations



Courtesy of A. Gurevich

- * The mechanism of HFQS (high field Q-slope) is not clear yet.
- Residual surface defects produced by cold-work deformation during cavity fabrication.
 - & Grain boundaries, oxides, hydride, and dislocations
- * The role of these defect in surface superconductivity.



Methodology

- Heavily deformed Nb wire from high purity SRF Nb rod by deep wire-drawing to introduce high cold work effect.
- * For comparison, unstrained single and bi crytal sample from high purity (RRR >250) large grain Nb sheet.
- Optimized SRF Nb cavity surface treatment was applied to change surface properties.
- Surface roughness and strain microstructure by confocal microscopy and EBSD-OIM.
- AC susceptibility measurement for quantification of variation of surface superconductivity.



Nb wire fabrication by deep-drawing

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Annealed Nb rod starting $\emptyset^{\sim}0.428''(10.9 \text{ mm})$ & 6 ''in length (152.4 mm): starting with $\epsilon_0 = 0$

Final Nb size .044 (1.1 mm)

~ 90% reduction (ε₀~ 4.17)



Local misorientation map of cross section of an as-drawn wire by EBSD-OIM



High possibility of lower misorientation strained structures at GBs



A series of surface treatments to change the level of surface defects

The recipe of "optimized" SRF cavity treatments

by A. Dzyuba @ FNAL





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EP and BCP improved surface uniformity





2hrs EP'ed

Shrs EP'ed

Roughness evaluated by SLCM (Scanning Laser Confocal Microscopy)

50 min EP'ed: 18.07 ± 0.19 μm 2 hrs EP'ed: 2.21 ± 0.14 μm

3 hrs EP'ed: 1.67 ± 0.08 μm





IPF map of the surface of EP'ed wires by EBSD-OIM

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IPF map



Reduction of local surface strain effect after 120°C/48h, but Redistribution by 800°C/2h HT



Local misorientation map shows the density of dislocations on the surface



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Cross sectional EBSDOIM for strained gradient of 800°C/2h HT'ed wires



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The onset of T_c varies by surface effect on AC susceptibility measurement

Another bump appears after 120°C/48hrs HT



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The onset of H_{c3} also changed by surface pinning effect



Surface effect disappears after 800°C/2h HT





No extra surface layer effect on T_c transition of BCP'ed single and bi-Xtal after 125°C/48hr HT







No extra surface layer effect on the onset of H_{c3} of BCP'ed single and bi-Xtal after 125°C/48hr HT





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	T _c [K]	ΔT [K]	H _{c2} at 5K [Oe]	H _{c3} at 5K [Oe]	r ₃₂ at 5K [H _{c3} /H _{c2}]
50 min EP	9.32	0.10	3598	6990	1.943
2 hrs EP	9.32	0.09	3825	7359	1.924
3 hrs EP	9.33	0.08	3986	6719	1.686
50 min EP + 120°C HT	9.29	0.14	4314	7631	1.769
2 hrs EP + 120°C HT	9.30	0.15	4175	7576	1.814
3 hrs EP + 120°C HT	9.30	0.12	3553	7281	2.049
50 min EP + 800°C HT	9.22	0.17	3931	7631	1.941
2 hrs EP + 800°C HT	9.22	0.15	4092	6931	1.694
3 hrs EP + 800°C HT	9.22	0.16	4470	6903	1.544



Conclusion

- Strained grain boundaries or GNB, or strained layers highly enhance impurities migration to the surface layer.
- K Longer EP and high temp baking returns r₃₂ to GL value (≈1.695) or even lower.
- Migration of impurities (H or O) to the surface layer may increase by mild baking then reduce H_{c3} values.
- 800°C/2hrs HT is enough to clean the surface. However, it may not be enough to get rid of all impurities in the wire.
- **Is H_{c3} increase by surface pinning good or bad to SRF?**
 - **Higher H**_{c3} is desirable for better surface superconductivity.
 - ***** But more pinning sites may increase surface residual resistivity.





Dislocation structures as interstitial super highways versus the passive Nb oxide

Only GBs? Or Dislocations at GBs?, but surface Oxide layers?



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AC Susceptibility measurement enables measurement of H_{c3} (Surface superconductivity)



2.5mm by 2.8mm disk-shape by MPMS2



Ø~0.8mm l~8mm wire-shape by PPMS



Surface pinning effect on Hc3 also revealed by varying AC amplitude and frequency

Onset of H_{c3} vary by surface pinning effects





The ratio (r_{32}) of H_{c3} to H_{c2} of SRF-processed Nb deviate markedly from the GL values of 1.695



2.5mm by 2.8mm disk-shape by MPMS2

Table 3							
The ratio	r ₃₂	=	B_{c3}	$/B_{c2}$	for	all	samples

Sample	$r_{32} = B_{c3}/B_{c2}$
BCP only	1.86 ± 0.03
BCP + baking	
BCP + 24 h 100 °C	1.93 ± 0.05
BCP + 48 h 100 °C	1.93 ± 0.05
BCP + 96 h 100 °C	1.93 ± 0.05
BCP + 48 h 120 °C	2.16 ± 0.03
BCP + 24 h 123 °C	2.17 ± 0.05
BCP + 48 h 123 °C	2.33 ± 0.05
BCP + 96 h 123 °C	2.32 ± 0.05
BCP + 24 h 144 °C	2.59 ± 0.05
BCP + 48 h 144 °C	2.59 ± 0.05
BCP + 96 h 144 °C	2.59 ± 0.05
BCP + baking + BCP	
BCP + 48 h 120 °C + 1 μ mBCP	1.90 ± 0.03
BCP + 48 h 120 °C + 5 μm BCP	1.87 ± 0.03
BCP + 48 h 120 °C + 10 μm BCP	1.86 ± 0.03
BCP + EP	
$BCP + 40 \mu m EP$	1.92 ± 0.05
$BCP + 80 \mu m EP$	2.10 ± 0.03
$BCP + 145 \mu m EP$	1.99 ± 0.05
$BCP + 165 \mu m EP$	1.99 ± 0.05
BCP + EP + baking	
BCP + 40 μm EP + 48 h 123 °C	2.64 ± 0.05
$BCP + 80 \mu m EP + 48 h 123 ^{\circ}C$	2.57 ± 0.05
$BCP + 145 \mu m EP + 48 h 123 ^{\circ}C$	2.40 ± 0.05
BCP + 165 µm EP + 48 h 123 °C	2.40 ± 0.05



Does grain boundary make this layer on surface superconductivity?



Overview of the as-received niobium slice

Preferential flux flow on the deep GB groove by transport characterization



• Flux flow evidence from H = 0.08 T to 0.28 T

